

IN THE CLAIMS:

Please amend the claims as follows:

1. (Currently Amended) A semiconductor device having a portion thereof formed from a wafer of semiconductive material by a laser etching process comprising:
a substrate of semiconductive wafer material having a surface ~~having a roughened surface thereon formed by a laser;~~
an interposer connected to the substrate, the interposer having a roughened surface formed by a laser increasing the surface area thereof to adhere mold material thereto in a molding operation;
and
resist on at least a portion of the surface of the substrate of semiconductive wafer material having a portion thereof removed by etching the resist from the surface of the substrate using a laser.
2. (Previously Presented) The semiconductor device according to claim 1, wherein the laser comprises a laser associated with an automolding system.
3. (Previously Presented) The semiconductor device according to claim 1, wherein the laser includes one of an Nd:YAG laser and an excimer laser.
4. (Previously Presented) The semiconductor device according to claim 1, wherein the substrate comprises a ball-grid-array substrate.
5. (Previously Presented) The semiconductor device according to claim 1, further comprising a vision system for detecting the resist.
6. (Previously Presented) The semiconductor device according to claim 5, wherein the vision system comprises:
a laser scanning system for detecting changes in a pattern of the substrate.

7 - 11 (Canceled)

12. (Currently Amended) A semiconductor device having a portion formed by a laser etching process on a substrate of semiconductive material having a surface comprising: resist located on at least a portion of the surface having a portion thereof removed by etching the resist from the at least a portion of the surface of the substrate using a laser forming a roughened surface on the surface of the substrate of semiconductive material increasing the surface area of the surface to adhere mold material thereto .

13. (Previously Presented) The semiconductor device according to claim 12, wherein the laser comprises a laser associated with an automolding system.

14. (Previously Presented) The semiconductor device according to claim 12, wherein the laser includes one of an Nd:YAG laser and an excimer laser.

15. (Previously Presented) The semiconductor device according to claim 12, wherein the substrate comprises a ball-grid-array substrate.

16. (Previously Presented) The semiconductor device according to claim 12, further comprising a vision system for detecting the resist.

17. (Previously Presented) The semiconductor device according to claim 16, wherein the vision system comprises: a laser scanning system for detecting changes in a pattern of the substrate.